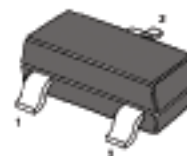


**NPN Silicon Epitaxial Planar Transistor**

for high voltage switching and amplifier applications.


 1. Base 2. Emitter 3. Collector  
 SOT-23 Plastic Package

**Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )**

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	500	V
Collector Emitter Voltage	$V_{CEO}$	400	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	300	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

**Characteristics at  $T_a = 25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $V_{CE} = 10\text{ V}$ , $I_C = 1\text{ mA}$	$h_{FE}$	40	-	-
at $V_{CE} = 10\text{ V}$ , $I_C = 10\text{ mA}$	$h_{FE}$	50	200	-
at $V_{CE} = 10\text{ V}$ , $I_C = 50\text{ mA}$	$h_{FE}$	45	-	-
at $V_{CE} = 10\text{ V}$ , $I_C = 100\text{ mA}$	$h_{FE}$	40	-	-
Collector Base Cutoff Current at $V_{CB} = 400\text{ V}$	$I_{CBO}$	-	0.1	$\mu\text{A}$
Collector Emitter Cutoff Current at $V_{CE} = 400\text{ V}$	$I_{CEO}$	-	0.5	$\mu\text{A}$
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	$I_{EBO}$	-	0.1	$\mu\text{A}$
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	500	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	400	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage				
at $I_C = 1\text{ mA}$ , $I_B = 0.1\text{ mA}$	$V_{CE(sat)}$	-	0.4	V
at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.5	V
at $I_C = 50\text{ mA}$ , $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.75	V
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$	$V_{BE(sat)}$	-	0.75	V
Collector Output Capacitance at $V_{CB} = 20\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	7	pF

